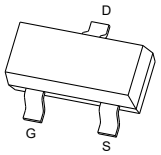
TKMP3401A

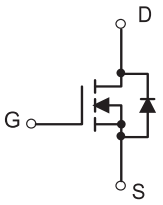
P-Channel 30-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
-30 V	55 mΩ@-10 V	-4.2
	68 mΩ@-4.5V	
	90mΩ@-2.5V	

SOT-23



Schematic diagram



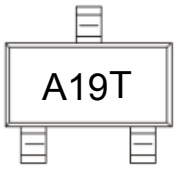
FEATURE

- TrenchFET Power MOSFET

APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING



Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±12	
Continuous Drain Current	I_D	-4.2	A
Pulsed Drain Current	I_{DM}	-30	
Maximum Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient(t ≤5s)	$R_{\theta JA}$	357	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55~+150	

MOSFET ELECTRICAL CHARACTERISTICS

T_a=25℃ unless otherwise specified

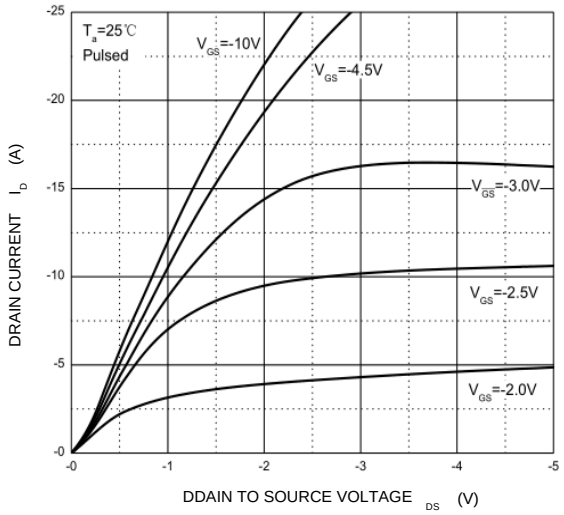
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-30	-32.2		V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.7	-0.8	-1.3	
Gate-source leakage	I_{GSS}	V_{DS} =0V, V_{GS} =±12V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} =-24V, V_{GS} =0V			-1	μA
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} =-10V, I_D =-4.2A		39	55	mΩ
		V_{GS} =-4.5V, I_D =-4.0A		57	68	
		V_{GS} =-2.5V, I_D =-1.0A		74	90	
Forward transconductance [a]	g_{fs}	V_{DS} =-5V, I_D =-5A		7		S
Dynamic[b]						
Input capacitance	C_{iss}	V_{DS} =-15V,V_{GS} =0V,f =1MHz		954		pF
Output capacitance	C_{oss}			115		
Reverse transfer capacitance	C_{rss}			77		
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	V_{GS}=-10V, V_{DS} =-15V R_L=3.6Ω, R_{GEN}=6Ω			6.3	ns
Rise time	t_r				3.2	
Turn-off delay time	$t_{d(off)}$				38.2	
Fall time	t_f				12	
Drain-source body diode characteristics						
Pulse diode forward current [a]	I_{SM}					A
Body diode voltage	V_{SD}	I_S=-1A		-0.8	-1.0	V

Notes :

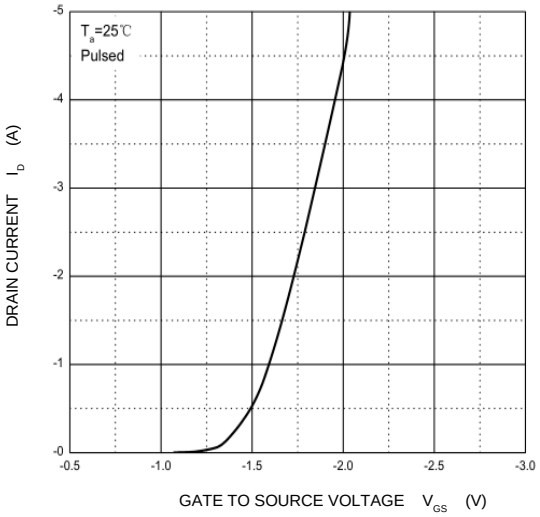
a.Pulse Test : Pulse Width < 300μs, Duty Cycle ≤2%.

b.Guaranteed by design, not subject to production testing.

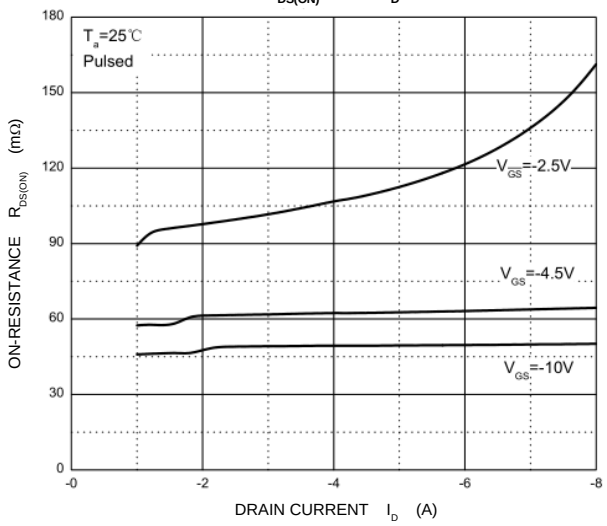
Output Characteristics



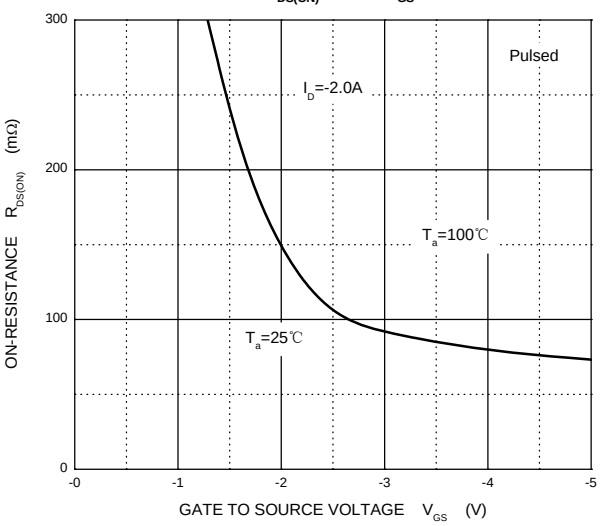
Transfer Characteristics



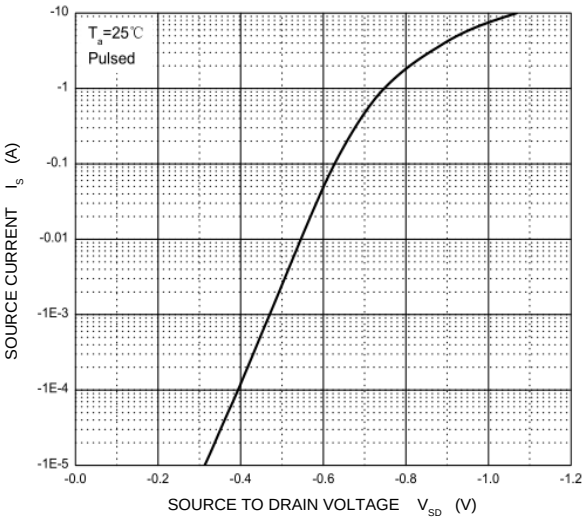
$R_{DS(ON)}$ —— I_D



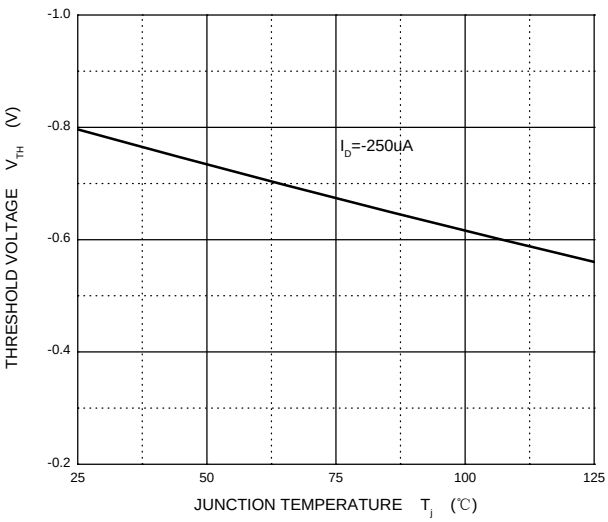
$R_{DS(ON)}$ —— V_{GS}

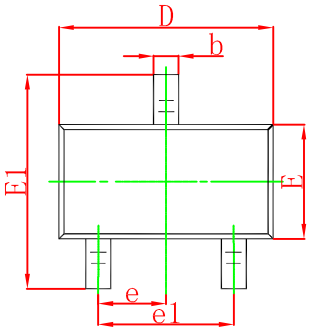


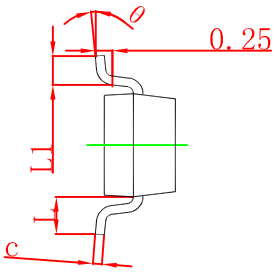
I_S —— V_{SD}

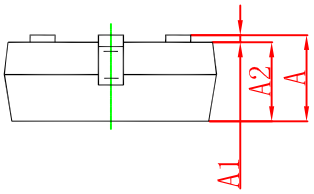


Threshold Voltage



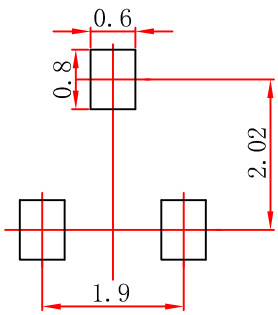






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.